

ABSTRACT

The present invention relates to a polishing method and a polishing apparatus for polishing a substrate, such as a wafer. The present invention further relates to a computer-readable storage medium storing a program for causing the polishing apparatus
5 to perform the polishing method. The polishing method includes: rotating a polishing table (3); and polishing a substrate (W) by pressing the substrate (W) against a polishing surface (2a). Polishing the substrate (W) includes a film-thickness profile adjustment process and a polishing-end-point detection process. The film-thickness profile adjustment process includes adjusting pressing forces on the substrate (W) against the
10 polishing surface (2a) based on a plurality of film thicknesses, and determining a point in time at which a film-thickness index value has reached a film-thickness threshold value. The film-thickness index value is determined from at least one of the plurality of film thicknesses. The polishing-end-point detection process includes measuring a torque for rotating the polishing table (3) and determining a polishing end point based on the torque.

Fig. 6